

100mA 30V(0.28mm)

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Chip Information

Chip Size	0.31 x 0.26mm
Pad Size	0.19 x 0.14mm
Chip Quantity	137348 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	30	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	30	V	
Average Forward Rectified Current	IF(AV)	100	mA	
Peak Forward Surge Current	IFSM	0.5	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.450	0.440	0.400	V	IF=10mA Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	0.5	0.3	0.02	uA	VR=10V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	30	35	50	V	IR=10uA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
XFC248	95 +/- 15um	Ti-Ni-Ag(For Ag Epoxy)
XFC249	100 +/- 15um	Au(For Eutectic)

Note:
Designed For RB520CS-30